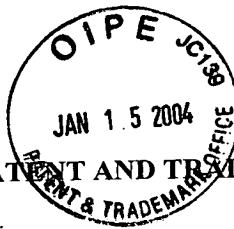


Docket No. 246179US90DIV



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Hiroyuki NAGASAWA, et al.

SERIAL NO: 10/734,221

GAU:

FILED: December 15, 2003

EXAMINER:

FOR: COMPOUND CRYSTAL AND METHOD OF MANUFACTURING SAME

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- ☒ The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are NOT attached, because they have been previously cited in parent application no. 10/140,187, filed May 8, 2002.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- ☐ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- ☐ Each item of information contained in this information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,
MAIER & NEUSTADT, P.C.

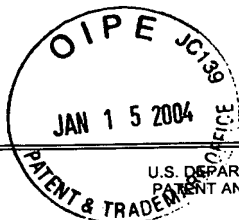
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Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 246179US90DIV		SERIAL NO. 10/734,221	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Hiroyuki NAGASAWA, et al.			
				FILING DATE December 15, 2003		GROUP	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA	6,051,849	04-2000	DAVIS ET AL.			
	AB	5,471,946	12-1995	SCHOLZ ET AL.			
	AC	6,184,144	02-2001	LO			
	AD	US005230768A	07-1993	FURUKAWA ET AL.			
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	AL	US20030047129A1	03-2003	KAWAHARA ET AL.			
	AM						
	AN						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO		
	AO	6-41400	06-1994	JAPAN (with English Abstract)			X
	AP	7-335562	12-1995	JAPAN (with partial English Abstract)			
	AQ	EP0743727A1	11-1996	EUROPE			
	AR						
	AS						
	AT						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
	AU	H. NAGASAWA ET AL., Materials Science Forum, Vols. 389-393, pgs 319-322, "HETEROEPITAXIAL GROWTH AND CHARACTERISTICS OF 3C-SiC ON LARGE-DIAMETER Si(001)SUBSTRATES," 2002					
	AV	A. NAGAYAMA ET AL., Phys. Stat. Sol. (a), Vol. 176, pgs. 513-517, "SUBSTRATE MISORIENTATION DEPENDENCE OF THE HEXAGONAL PHASE INCLUSION IN CUBIC GaN FILMS GROWN BY METALORGANIC VAPOR PHASE EPITAXY," 1999					
	AW	C. LONG ET AL., Journal of Applied Physics, Vol. 86, No. 5, pps. 2509-2515, XP-000934896, "STRUCTURAL DEFECTS IN 3C-SiC GROWN ON Si BY SUPERSONIC JET EPITAXY", September 1, 1999.					
	AX	Y. V. MELNIK ET AL., Diamond and Related Materials, Vol. 6, No. 10, pgs. 1532-1535, XP-004096982, "STRUCTURAL PROPERTIES OF GaN GROWN ON SiC SUBSTRATES BY HYDRIDE VAPOR PHASE EPITAXY", August 1, 1997.				<input type="checkbox"/> Additional References sheet(s) attached	
	AY	H. D. CHO ET AL., Journal of Crystal Growth, Vol. 175-175, No. 3001, pgs. 125-128, XP-004091279, "ZINC BLENDE GaN GROWN BY RADIO FREQUENCY PLASMA ASSISTED MOLECULAR BEAM EPITAXY", May 1, 1997.					
Examiner					Date Considered		
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							